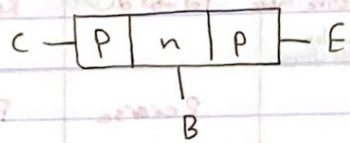
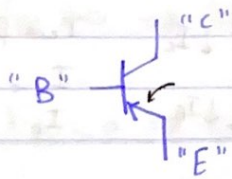
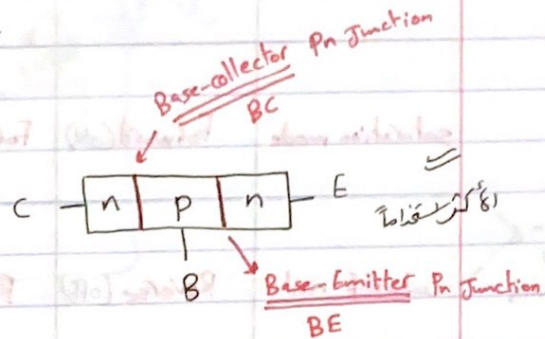
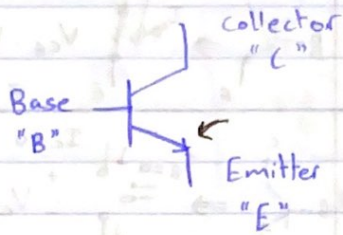
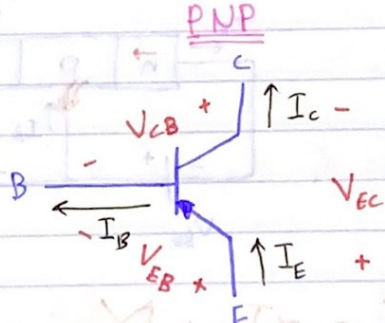
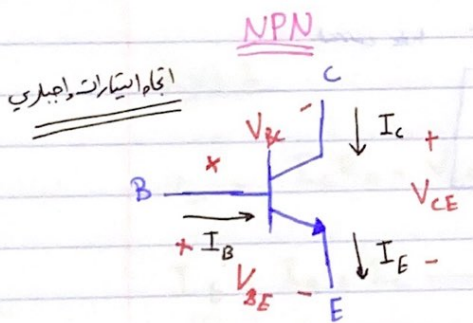


T₆ : BJT Construction & Operation

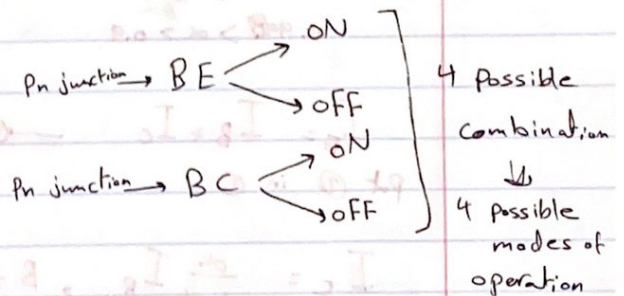
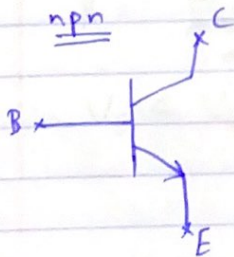
* Bipolar Junction Transistor



⇒ Transistor structure



⇒ Transistor Biasing

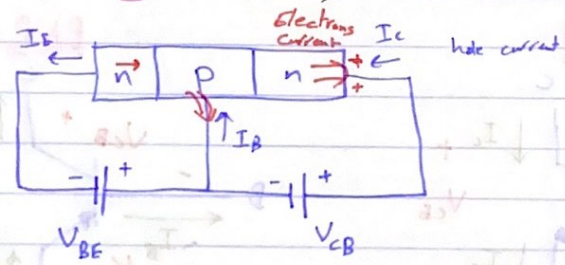


Junction/Mode	BE	BC	
saturation mode	Forward (ON)	Forward (ON)	
cut-off mode	Reverse (OFF)	Reverse (OFF)	
linear (Active) mode	Forward (ON)	Reverse (OFF)	
	Reverse	Forward	

used in digital Electronics

* * linear (Active) mode Amplifiers ⇒ used in analog electronics

⇒ In active region



$$I_C = \alpha I_E + I_{BO} \quad \text{--- (1)}$$

majority minority

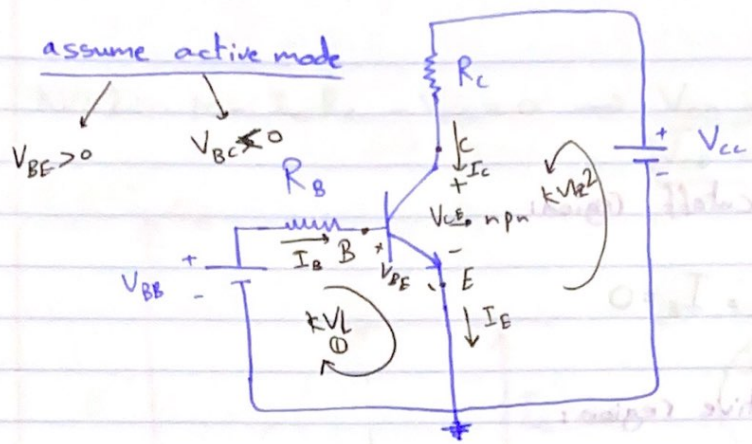
$$0.99 > \alpha > 0.9$$

$$I_E = I_B + I_C \quad \text{--- (2)}$$

put (2) in (1)

$$I_C = \frac{\alpha}{1-\alpha} I_B, \quad \beta = \frac{\alpha}{1-\alpha}$$

$$\Rightarrow I_C = \beta I_B$$



$V_{BE} > 0 \Rightarrow BE \rightarrow ON$

$V_{BC} < 0 \Rightarrow BC \rightarrow OFF$

KVL1

$V_{BB} = I_B R_B + V_{BE} \quad \text{--- ①}$

KVL2

$V_{CC} = I_C R_C + V_{CE} \quad \text{--- ②}$

$I_E = I_B + I_C \quad \text{--- ③}$

$\alpha = \frac{I_C}{I_E} \quad \text{--- ④}$

$\beta = \frac{I_C}{I_B} \quad \text{--- ⑤}$

$\beta = \frac{\alpha}{1-\alpha} \quad \text{--- ⑥}$

$V_E < V_B < V_C$

* Summary

• In the cutoff region:

$$I_B = I_C = I_E = 0$$

• In the active region:

$$I_C = \alpha I_E$$

$$I_C = \beta I_B$$

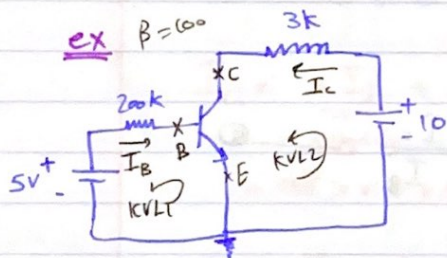
$$I_E = (\beta + 1) I_B$$

$$\text{npn, Si} \Rightarrow V_{BE} = 0.7V$$

$$\text{pnp, Si} \Rightarrow V_{BE} = -0.7V$$

$$V_{CE} > V_{CE,sat} = 0.2V, \text{ npn}$$

$$V_{CE} < V_{CE,sat} = -0.2V, \text{ pnp}$$



Find mode of operation of BJT, I_C , V_{CE} .

BE → FW

BC (FW)

↓
saturation

BC (BW)

↓
Active

• Assume BJT is in active mode:

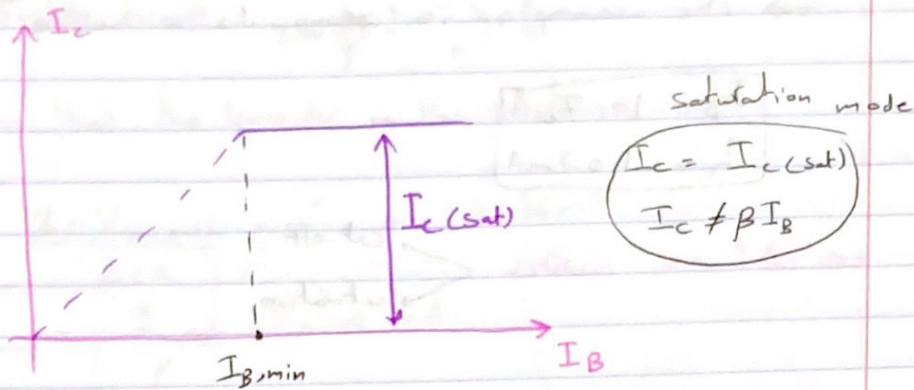
KVL: $5 - I_B \cdot 200k - V_{BE} = 0 \rightarrow V_{BE} = 0.7 \leftarrow \text{active}$

$$\therefore I_B = \frac{5 - 0.7}{200k} = 21.5 \mu\text{A}$$

$$I_C = \beta I_B = 2.15 \text{ mA}$$

$$\text{KVL2: } 10 - I_c R_c - V_{CE} = 0 \rightarrow V_{CE} = 10 - 2.15 \times 3k$$

$$V_{CE} = 3.55V$$



$$V_{CE} = V_{CC} - I_c R_c$$

$$\therefore I_{c(sat)} = \frac{V_{CC} - V_{CE(sat)}}{R_c}$$

$$I_{B(min)} = \frac{I_{c(sat)}}{\beta}$$

\Rightarrow If $I_B > I_{B(min)} \Rightarrow$ saturation mode

\Rightarrow If $I_B < I_{B(min)} \Rightarrow$ Active region

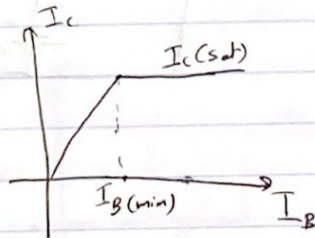
• Assume saturation mode:

$$V_{CE} = V_{CE(sat)} = 0.2V, \quad I_c = I_{c(sat)} = ?$$

$$10 = I_c \cdot 3k + I_b \cdot 2k$$

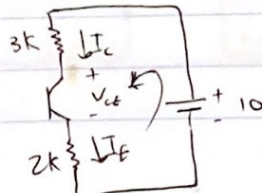
in saturation:

$$I_c \approx I_E = I_{c(sat)}, \quad V_{CE} = V_{CE(sat)} = 0.2$$



$$\therefore I_{c(sat)} = \frac{10 - 0.2}{3k + 2k} = 1.96 \text{ mA}$$

$$I_{B(min)} = \frac{I_{c(sat)}}{\beta} = 19.6 \text{ }\mu\text{A}$$



→ Find $I_{B(\text{actual})} = \frac{5 - 0.7}{20k + 2k(10)} = 10.7 \mu A < I_{B(\text{min})}$

→ The assumption is wrong, it's in active mode.

$$\begin{aligned} I_B &= 10.7 \mu A \\ I_C &= 1.07 \text{ mA} \end{aligned}$$

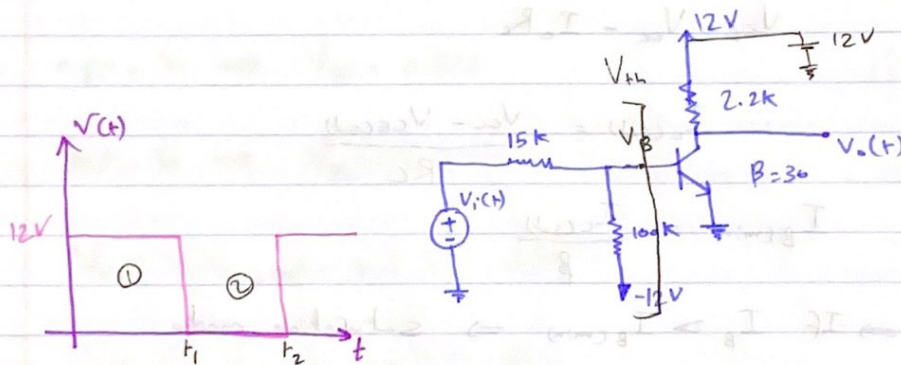
17:01

⇒ BJT as switch

cut-off

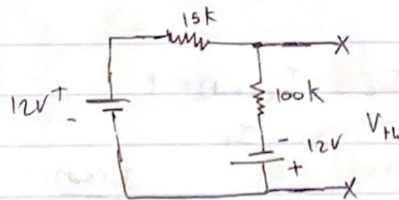
saturation

ex Find $V_o(t)$ for the input given below:



① $0 - t_1 \Rightarrow V_i = 12V$

To Find V_{th} & R_{th}



super position

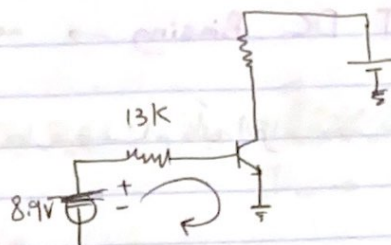
$$V_{th}^I = \frac{15k}{(15+100)k} \times 12V$$

$$V_{th}^{II} = \frac{100k}{(15+100)k} \times (-12V)$$

$$V_{th} = V_{th}^I + V_{th}^{II} = 8.9V$$

$$R_{th} = 100k // 15k = 13k$$

Base-Emitter: Forward



Assume that the transistor is in the saturation mode

$$\frac{12 - V_{CE(sat)}}{2.2k} = I_{C(sat)} = 5.36 \text{ mA}$$

$$I_{B(min)} = \frac{I_{C(sat)}}{\beta} = 0.18 \text{ mA}$$

$$I_{B(actual)} = \frac{V_{th} - V_{BE}}{13k} = \frac{8.9 - 0.7}{13k} = 0.63 \text{ mA}$$

Since $I_B > I_{B(min)}$, our assumption is right

$$V_{CE(sat)} = V_o = 0.2 \text{ V}$$

$$I_C = 5.36 \text{ mA}$$

② $t_1 - t_2 \Rightarrow V_i = 0 \text{ Volt}$

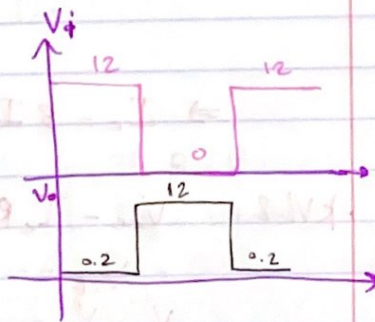
$$V_{th} = \frac{15}{15+100} \times 12 = -1.56 \text{ V}$$

$$R_{th} = 13k$$

Base-Emitter: Reverse
cutoff region

$$I_B = 0 \Rightarrow V_o = V_{CE} = 12 \text{ V}$$

inverter/not gate



T7: BJT DC Biasing → active/linear mode

البياس في مدار فولتية خارجية عن طريق الترانزيستور يشغل بالمواد التي
 أيضا بنا الال. *(Handwritten note in Arabic)*

① Fixed-bias circuit

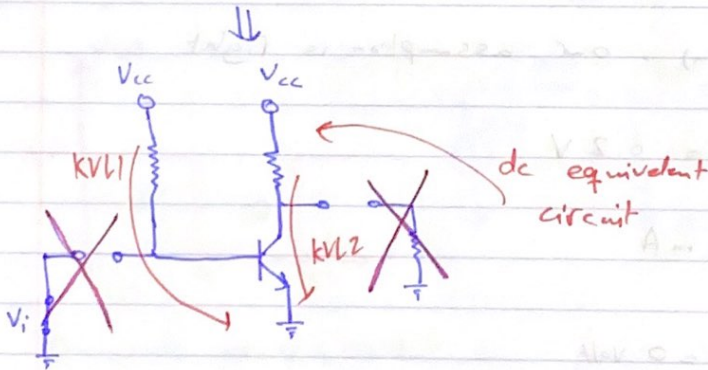
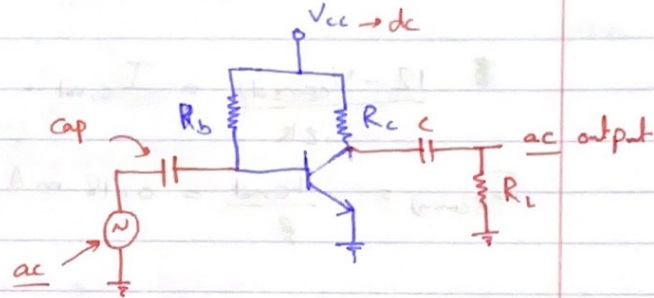
dc Analysis

⇒ ac sources killed

⇒ $f=0$

$$X_c = \frac{1}{2\pi f c} \approx \infty$$

caps are treated as open circuit



• KVL1: $V_{cc} - I_B R_B - V_{BE} = 0$

$$\Rightarrow I_B = \frac{V_{cc} - V_{BE}}{R_B}$$

(Handwritten note in Arabic): أيضا قيمة R_B هو اي I_B يزيدنا قيمة I_B .
 قيمة I_B I_C نزيدنا قيمة I_C .

$$\Rightarrow I_C = \beta I_B$$

• KVL2: $V_{cc} - I_C R_C - V_{CE} = 0$

$$V_{CE} = V_{cc} - I_C R_C$$

$$V_C - V_E = V_{cc} - I_C R_C$$

$$V_E = 0$$

$$\Rightarrow V_C = V_{CC} - I_C R_C \rightarrow \text{~~scribble~~}$$

$$I_C = \frac{V_{CC} - V_{CE}}{R_C}$$

$$V_{BE} = V_B - V_E$$

$$V_E = 0$$

$$\therefore V_{BE} = V_B$$

$$V_{BE} - V_{CE} - V_{BC} = 0$$

$$\therefore V_{BC} = V_{BE} - V_{CE}$$

ex $V_{CC} = 10V$, $\beta_{nominal} = 100$, $\beta_{min} = 50$, $\beta_{max} = 150$
 $V_{CEQ} = 5V$, $I_{CQ} = 1mA$
 Find R_B & R_C

$$I_B = \frac{I_C}{\beta} = \frac{1mA}{100} = 10\mu A$$

$$I_B = \frac{V_{CC} - V_{BE}}{R_B}$$

$$10\mu = \frac{10 - 0.7}{R_B}$$

$$R_B = 930k\Omega$$

$$V_{CE} = V_{CC} - I_C R_C$$

$$R_C = \frac{V_{CC} - V_{CE}}{I_C} = \frac{10 - 5}{1mA} = 5k\Omega$$

$$R_C = 5k\Omega$$

• If $\beta = \beta_{min} = 50$

$$I_B = 10\mu A \text{ (constant)}$$

$$I_C = \beta I_B = 50(10\mu A) = 0.5mA$$

$$V_{CE} = V_{CC} - I_C R_C \Rightarrow V_{CE} = 7.5V$$

• If $\beta = \beta_{max}$

$$I_B = 10\mu A$$

$$I_C = \beta I_B = 1.5mA$$

$$V_{CE} = 2.5V$$

⇒ for $50 \leq \beta \leq 150$

$I_B = 10 \mu A$ - Fixed

$0.5 \text{ mA} \leq I_C \leq 1.5 \text{ mA}$

$2.5 \text{ V} \leq V_{CE} \leq 7.5 \text{ V}$

∴ $\frac{I_{C(\text{max})}}{I_{C(\text{min})}} = \frac{1.5 \text{ mA}}{0.5 \text{ mA}} = 3$ not very stable

⊙ Emitter - stabilized Bias circuit

* KVL⊙:

$V_{CC} - I_B R_B - V_{BE} - I_E R_E = 0$

$I_E = (\beta + 1) I_B$

⇒ $I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1) R_E}$

⇒ $I_E = \frac{V_{CC} - V_{BE}}{\frac{R_B}{\beta + 1} + R_E}$ (β is very large, so $\frac{R_B}{\beta + 1} \approx 0$)

$R_E \gg \frac{R_B}{\beta + 1}$

$I_E = \frac{V_{CC} - V_{BE}}{R_E}$ *

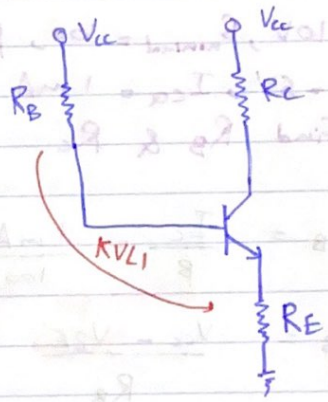
Design rule/Assumption: $0.1 V_{CC} \leq V_E \leq 0.2 V_{CC}$

(Design for V_{CE} , choose V_E and R_E and I_E)

* KVL⊙

$-V_{CC} + I_C R_C + V_{CE} + I_B R_B = 0$

since $I_E \approx I_C \Rightarrow V_{CE} = V_{CC} - I_C (R_C + R_E)$



ex $V_{CC} = 10V$, $\beta_{nominal} = 100$, $\beta_{min} = 50$, $\beta_{max} = 150$

$V_{CE} = 5V$, $I_C = 1mA$

• Assumption to be used in design problem only if R_E is unknown
o.l $V_{CC} \leq V_E \leq 0.2 V_{CC}$

① let $V_E = 0.1 V_{CC} = 1V$

$$I_E = \frac{V_E}{R_E}$$

$$R_E = \frac{1V}{0.99mA} \approx 1k\Omega = R_E$$

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)R_E}$$

$$R_B = 829k\Omega$$

$$R_C = \frac{V_{CC} - V_{CE} - V_E}{I_C} = \frac{10 - 5 - 1}{1mA} = 4k\Omega = R_C$$

• If $\beta = \beta_{min} = 50$

$$I_B = \frac{10 - 0.7}{829k + (51)(1k)} = 10.56 \mu A$$

$$I_C = \beta I_B = 0.528 mA$$

$$V_{CE} = V_{CC} - I_C R_C - V_E = 10 - (0.528m)(4k) - 1 = 6.89V = V_{CE}$$

• If $\beta = \beta_{max} = 150$

$$I_B = 9.489 \mu A$$

$$I_C = 1.423 mA$$

$$V_{CE} = 3.31V$$

for $50 \leq \beta \leq 150$

$$10.56 \mu A \geq I_B \geq 9.489 \mu A$$

$$1.423 mA \geq I_C \geq 0.528 mA$$

$$6.89V \geq V_{CE} \geq 3.31V$$

$$\frac{I_{C,max}}{I_{C,min}} = \frac{1.423}{0.528} \approx 2.7$$

Implicated
but not
very stable

③ DC Bias with voltage feedback

* KVL①

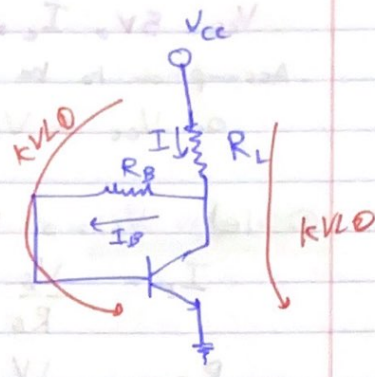
$$V_{CC} - I R_L - I_B R_B - V_{BE} = 0$$

$$I = I_C + I_B$$

$$I_C = \beta I_B$$

$$I = (\beta + 1) I_B$$

$$\Rightarrow I_B = \frac{V_{CC} - V_{BE}}{R_L(\beta + 1) + R_B}$$



* KVL②

$$V_{CC} = I R_L + V_{CE}$$

$$V_{CE} = V_{CC} - (I_C + I_B) R_L$$

ex $V_{CC} = 10V$, $\beta_{nominal} = 100$, $\beta_{min} = 50$, $\beta_{max} = 150$
 $V_{CE} = 5V$, $I_C = 1mA$

$$R_L = \frac{V_{CC} - V_{CE}}{I} = \frac{V_{CC} - V_{CE}}{I_B + I_C} = \frac{10 - 5}{1mA + \frac{1mA}{100}}$$

$$\Rightarrow R_L = 4.95k\Omega$$

$$I_B = \frac{V_{CC} - V_{BE}}{R_L(\beta + 1) + R_B} \Rightarrow 430k\Omega = R_B$$

• If $\beta = \beta_{min} = 50$

$$I_B = 0.013627 \text{ mA}$$

$$I_C = 0.68 \text{ mA}$$

• If $\beta = \beta_{max} = 150$

$$I_B = 0.00793 \text{ mA}$$

$$I_C = 1.19 \text{ mA}$$

for $50 \leq \beta \leq 150$

$$0.68 \text{ mA} \leq I_C \leq 1.19 \text{ mA}$$

$$\therefore \frac{I_{C(max)}}{I_{C(min)}} = \frac{1.19 \text{ mA}}{0.68 \text{ mA}} \approx 1.75 \quad \text{Better Q-point stability}$$

④ Voltage Divider Bias

• Approximate Analysis

$$I_B \ll I_1$$

$$I_2 = I_B + I_1 \Rightarrow I_2 \approx I_1$$

$$V_B = \frac{R_2}{R_1 + R_2} V_{CC}$$

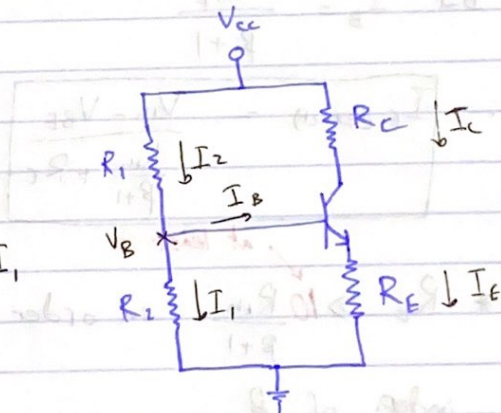
$$I_E (\text{approximate}) = \frac{V_E}{R_E} = \frac{V_B - V_{BE}}{R_E} \leftarrow \text{approx } \beta$$

KVL

$$V_{CE} = V_{CC} - I_C R_C - I_E R_E$$

$$I_E \approx I_C$$

$$V_{CE} = V_{CC} - I_C (R_C + R_E)$$



Exact Analysis

Thevenin Equivalent circuit for the circuit left

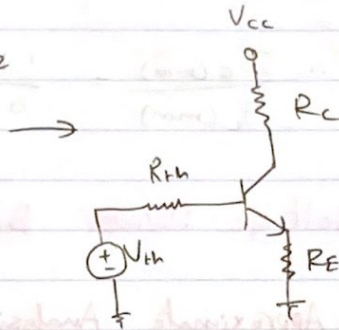
$$V_{th} = \frac{R_1 V_{cc}}{R_1 + R_2}$$

$$R_{th} = R_1 // R_2 = \frac{R_1 R_2}{R_1 + R_2}$$

$$V_{th} = I_B R_{th} + V_{BE} + I_E R_E$$

$$\text{but } I_B = \frac{I_E}{\beta + 1}$$

$$\therefore I_E (\text{exact}) = \frac{V_{th} - V_{BE}}{\frac{R_{th}}{\beta + 1} + R_E}$$



* $R_E \gg 10 \frac{R_{th}}{\beta + 1}$ ^{at least 10} in order to get I_E almost indep. of β

ex $V_{cc} = 10V$, $\beta_{nominal} = 100$, $\beta_{min} = 50$, $\beta_{max} = 150$
 $V_{CE} = 5V$, $I_E = 1mA$

① let $V_E = 0.1 V_{cc} \Rightarrow V_E = 1V$

$$I_E = \frac{V_E}{R_E} \Rightarrow R_E = \frac{1V}{1.01mA} \approx 1k\Omega$$

② let $R_{th} = \frac{R_E \cdot \beta_{nominal}}{50} = \frac{1k(100)}{50} = 2k\Omega$

③ $V_{cc} = R_C I_C + R_E I_E + V_{CE}$